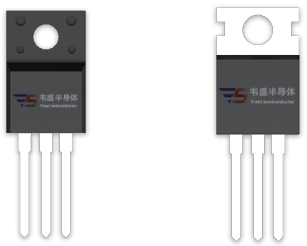
SBD20H100CT、SBDF20H100CT SCHOTTKY BARRIER RECTIFIER

MAIN CHARACTERISTICS

I_O	20(10×2)A
V_{RRM}	100 V
T_j	175 ℃
$V_{F(typ)}$	0.66V （@Tj=150℃）



TO-220F TO-220C

1.ANODE
2.CATHODE
3.ANODE

FEATURES

- Low Power Loss,High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	SBD		Unit
		20H100CT	F20H100CT	
V_{RRM}	Peak repetitive reverse voltage	100		V
V_{RWM}	Working peak reverse voltage			
V_R	DC blocking voltage			
$V_{R(RMS)}$	RMS reverse voltage	70		V
I_O	Average rectified output current	20		A
I_{FSM}	Non-Repetitive peak forward surge current (8.3ms half sine wave)	200		A
$R_{\Theta Jc}$	Thermal resistance from junction to case ,Tc=25℃	2.0	3.0	℃/W
$R_{\Theta JA}$	Thermal resistance from junction to ambient	75		℃/W
T_j	Junction temperature	175		℃
T_{stg}	Storage temperature	-55~+175		℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	I_R=0.1mA		100			V
Reverse current	I_R	V_R=100V	Tj =25℃		200	500	nA
			Tj =150℃		0.5		mA
Forward voltage	V_F	I_F=5A	Tj =25℃		0.75		V
			Tj =150℃		0.58		V
		I_F=10A	Tj =25℃		0.80	0.85	V
			Tj =150℃		0.66		V

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.

FIG.1: FORWARD CURRENT DERATING CURVE

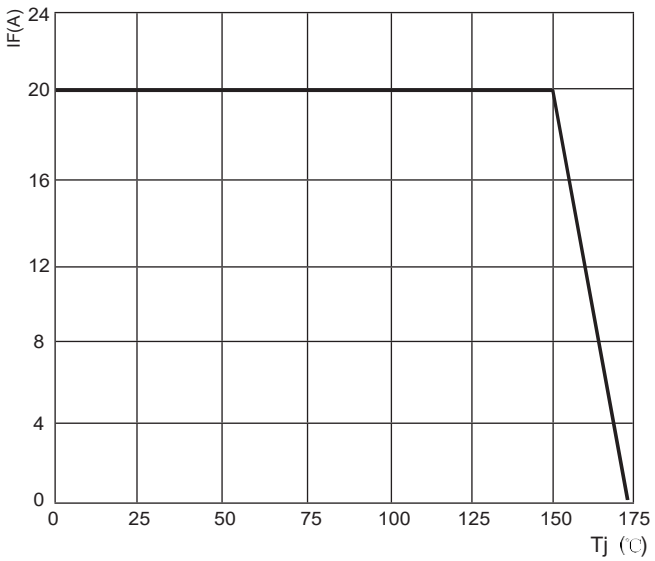


FIG.2: TYPICAL FORWARD CHARACTERISTICS

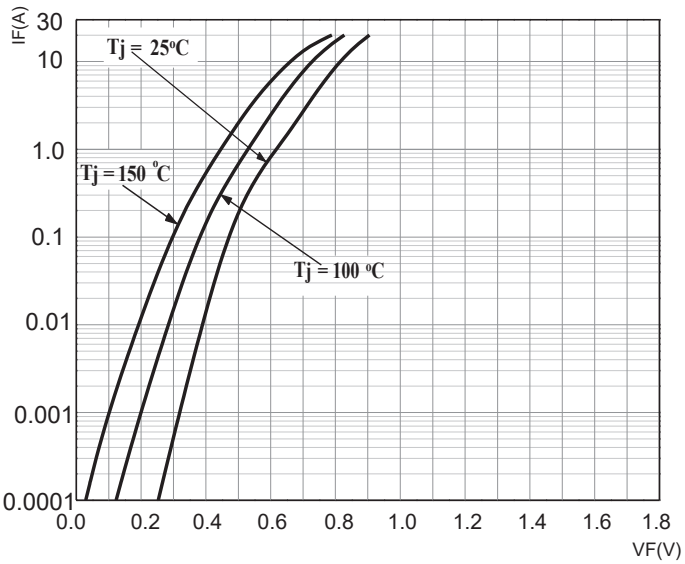


FIG.3: TOTAL CAPACITANCE DERATING CURVE

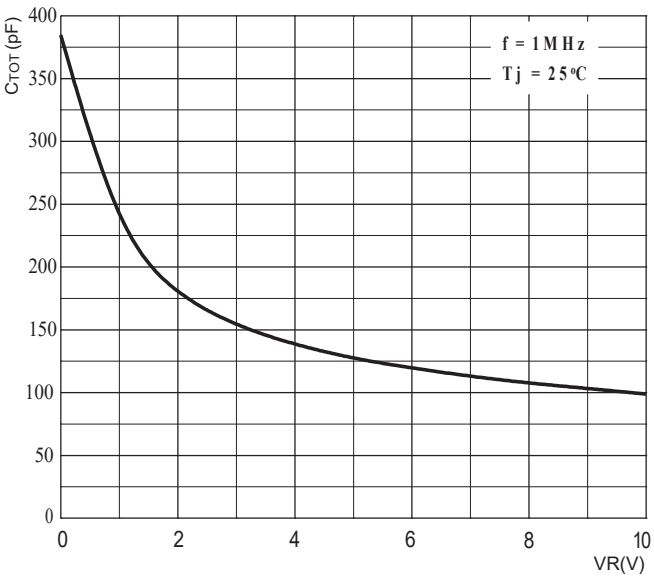


FIG.4: TYPICAL REVERSE CHARACTERISTICS